

Notice of References Cited	Application/Control No. 10/802,806	Applicant(s)/Patent Under Reexamination IZUMI ET AL.	
	Examiner Heather A. Doty	Art Unit 2813	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-5,759,908	06-1998	Steckl et al.	438/479
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Andrew J. Steckl and J.P. Li, "Epitaxial Growth of beta-SiC on Si by RTCVD with C3H8 and SiH4", IEEE Transactions on Electron Devices, Vol. 39, No. 1, January 1992, pgs. 64-74.
	V	
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.